



# M74HCT688

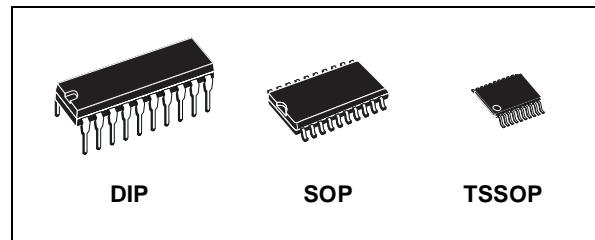
## 8 BIT EQUALITY COMPARATOR

- HIGH SPEED:  
 $t_{PD} = 21\text{ns}$  (TYP.) at  $V_{CC} = 4.5\text{V}$
- LOW POWER DISSIPATION:  
 $I_{CC} = 4\mu\text{A}$ (MAX.) at  $T_A=25^\circ\text{C}$
- COMPATIBLE WITH TTL OUTPUTS :  
 $V_{IH} = 2\text{V}$  (MIN.)  $V_{IL} = 0.8\text{V}$  (MAX)
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OHI}| = I_{OL} = 4\text{mA}$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \approx t_{PHL}$
- PIN AND FUNCTION COMPATIBLE WITH  
74 SERIES 688

### DESCRIPTION

The M74HCT688 is an high speed CMOS 8 BIT EQUALITY COMPARATOR fabricated with silicon gate C<sup>2</sup>MOS technology.

The M74HCT688 compares bit for bit two 8-bit words applied on inputs P0 - P7 and inputs Q0 - Q7 and indicates whether or not they are equal. A single active low enable is provided to facilitate



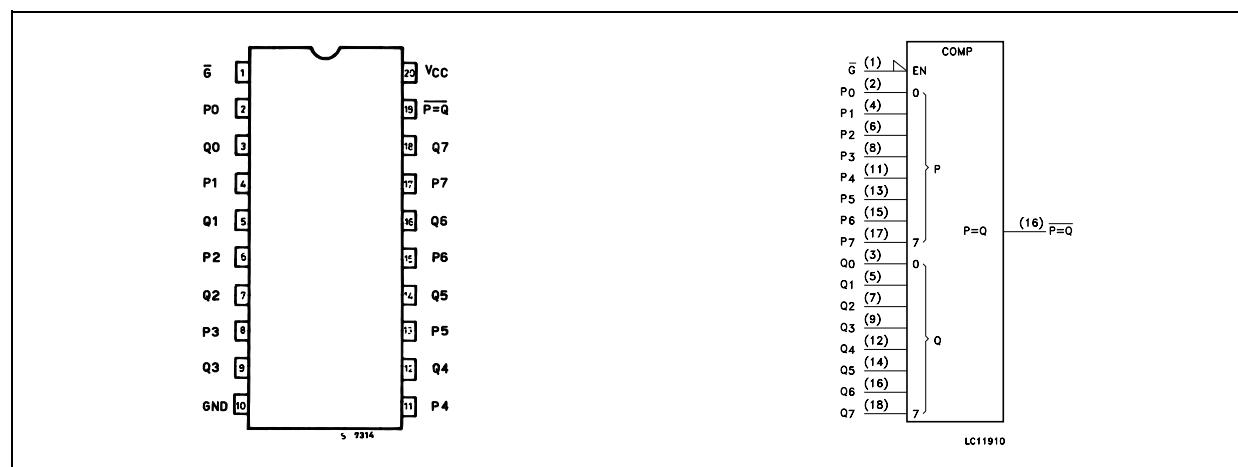
### ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HCT688B1R	
SOP	M74HCT688M1R	M74HCT688RM13TR
TSSOP		M74HCT688TTR

cascading several packages to enable comparison of words greater than 8 bits.

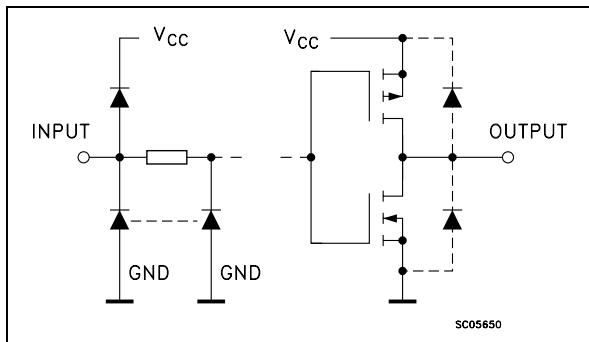
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



## M74HCT688

### INPUT AND OUTPUT EQUIVALENT CIRCUIT



### PIN DESCRIPTION

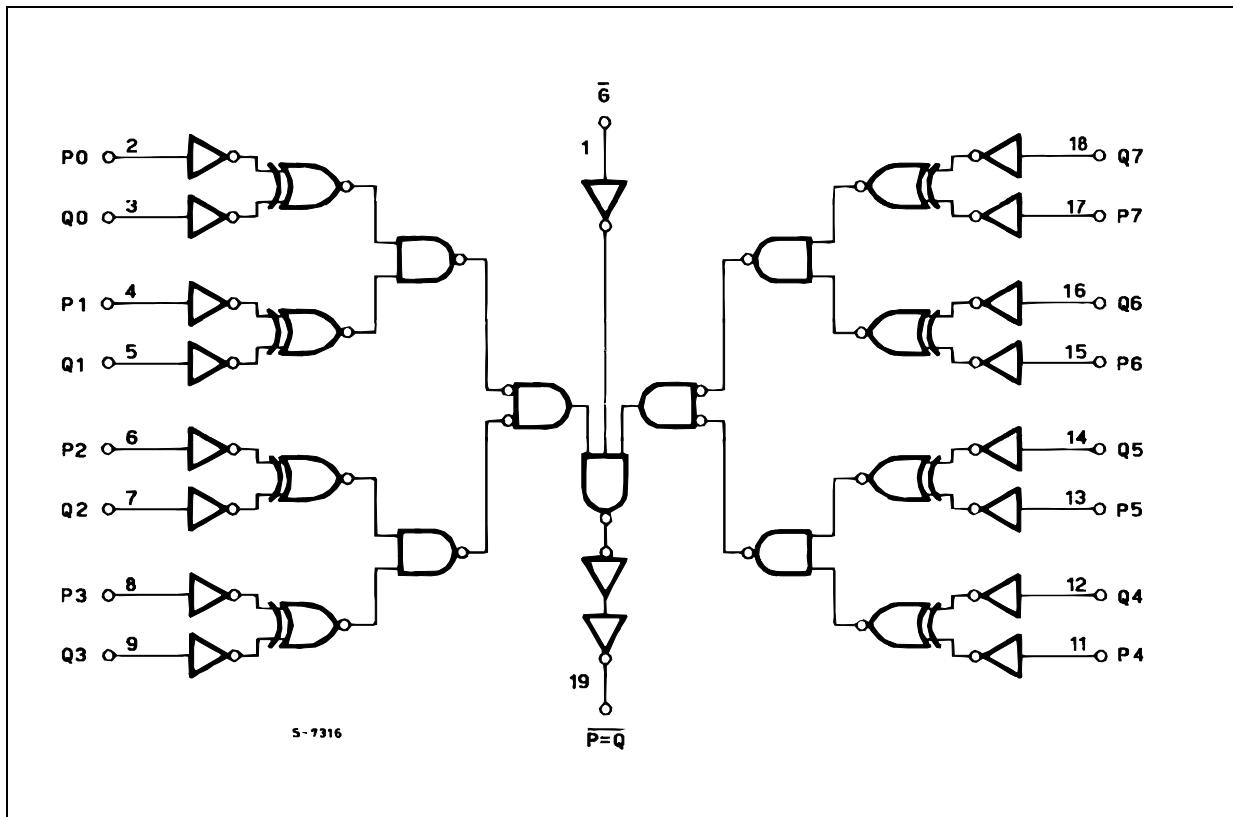
PIN No	SYMBOL	NAME AND FUNCTION
1	$\bar{G}$	Enable Input (Active LOW)
2, 4, 6, 8, 11, 13, 15, 17	$P_0$ to $P_7$	Word Inputs
3, 5, 7, 9, 12, 14, 16, 18	$Q_0$ to $Q_7$	Word Outputs
19	$P = Q$	Equal to Output
10	GND	Ground (0V)
20	$V_{CC}$	Positive Supply Voltage

### TRUTH TABLE

INPUTS		OUTPUT	
$P, Q$	$\bar{G}$	$\bar{P} = \bar{Q}$	$\overline{P = Q}$
$P = Q$	L	L	H
$P <> Q$	L	H	L
X	H	H	H

X: Don't Care

### LOGIC DIAGRAM



This logic diagram has not been used to estimate propagation delays

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	-0.5 to +7	V
$V_I$	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
$V_O$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	DC Input Diode Current	$\pm 20$	mA
$I_{OK}$	DC Output Diode Current	$\pm 20$	mA
$I_O$	DC Output Current	$\pm 25$	mA
$I_{CC}$ or $I_{GND}$	DC $V_{CC}$ or Ground Current	$\pm 50$	mA
$P_D$	Power Dissipation	500(*)	mW
$T_{stg}$	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	4.5 to 5.5	V
$V_I$	Input Voltage	0 to $V_{CC}$	V
$V_O$	Output Voltage	0 to $V_{CC}$	V
$T_{op}$	Operating Temperature	-55 to 125	°C
$t_r, t_f$	Input Rise and Fall Time ( $V_{CC} = 4.5$ to 5.5V)	0 to 500	ns

**DC SPECIFICATIONS**

Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ C$			$-40$ to $85^\circ C$		$-55$ to $125^\circ C$		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
$V_{IH}$	High Level Input Voltage	4.5 to 5.5		2.0			2.0		2.0		V
$V_{IL}$	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
$V_{OH}$	High Level Output Voltage	4.5	$I_O=-20 \mu A$	4.4	4.5		4.4		4.4		V
			$I_O=-4.0 \text{ mA}$	4.18	4.31		4.13		4.10		
$V_{OL}$	Low Level Output Voltage	4.5	$I_O=20 \mu A$		0.0	0.1		0.1		0.1	V
			$I_O=4.0 \text{ mA}$		0.17	0.26		0.33		0.40	
$I_I$	Input Leakage Current	5.5	$V_I = V_{CC}$ or GND			$\pm 0.1$		$\pm 1$		$\pm 1$	$\mu A$
$I_{CC}$	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			4		40		80	$\mu A$
$\Delta I_{CC}$	Additional Worst Case Supply Current	5.5	Per Input pin $V_I = 0.5V$ or $V_I = 2.4V$ Other Inputs at $V_{CC}$ or GND $I_O = 0$			2.0		2.9		3.0	mA

## M74HCT688

### AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6\text{ns}$ )

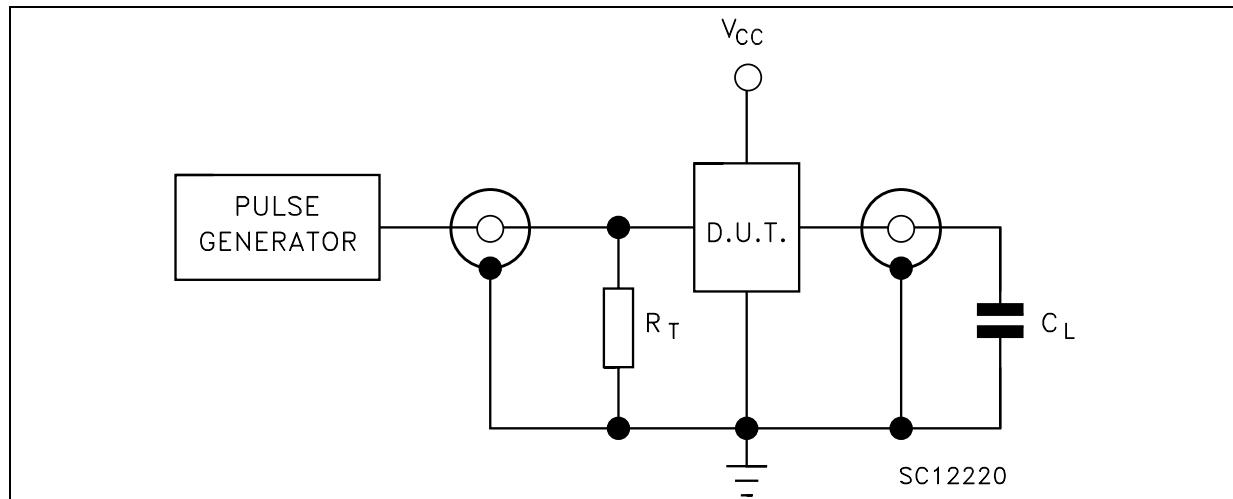
Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		
$t_{TLH} t_{THL}$	Output Transition Time	4.5			8	15		19		22 ns	
$t_{PLH} t_{PHL}$	Propagation Delay Time ( $P_n, Q_n - P=Q$ )	4.5			21	32		40		48 ns	
$t_{PLH} t_{PHL}$	Propagation Delay Time ( $G - P=Q$ )	4.5			15	23		29		35 ns	

### CAPACITIVE CHARACTERISTICS

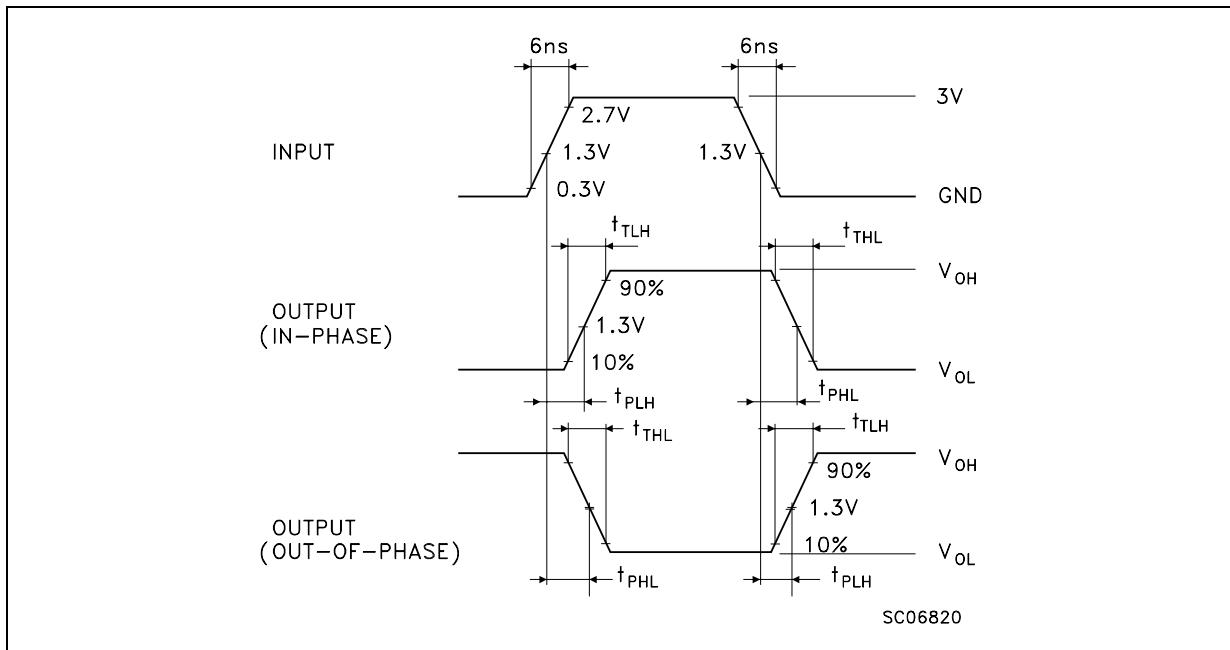
Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		
$C_{IN}$	Input Capacitance				5	10		10		10 pF	
$C_{PD}$	Power Dissipation Capacitance (note 1)				32					pF	

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(\text{opr})} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

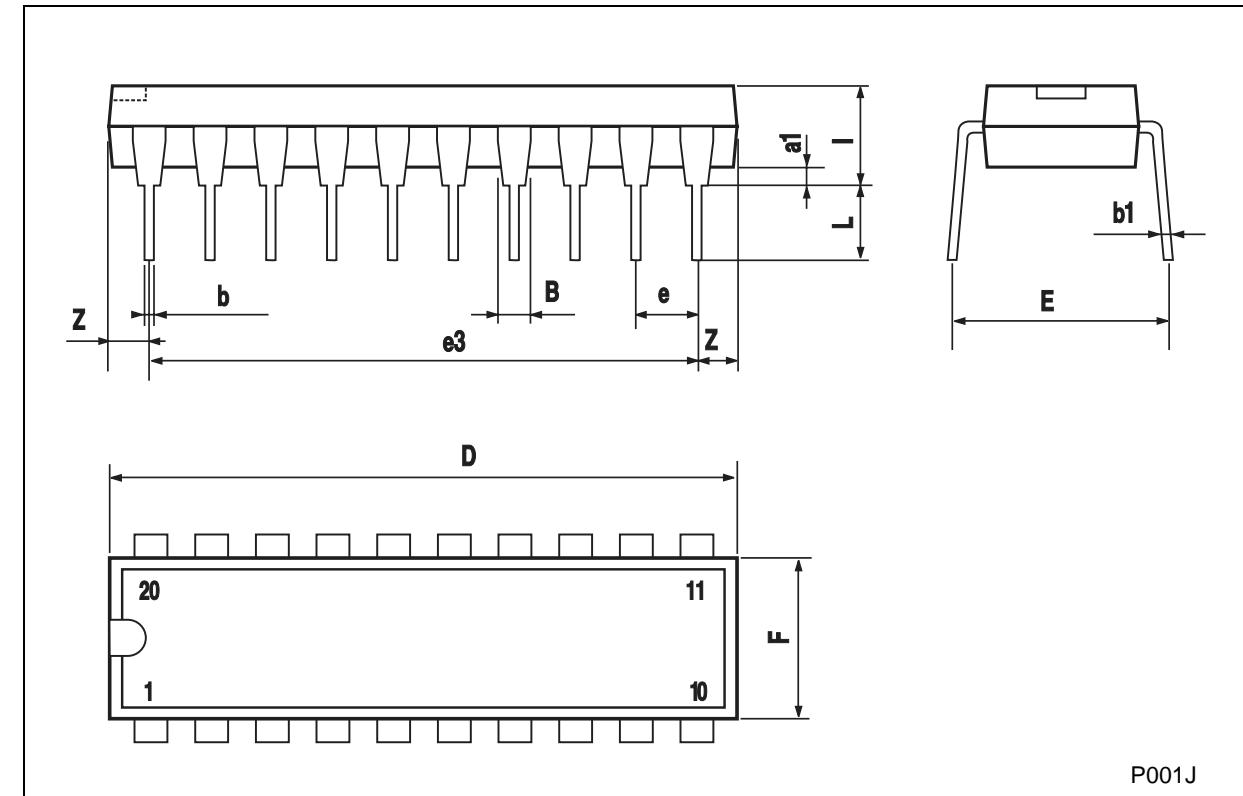
### TEST CIRCUIT



$C_L = 50\text{pF}/150\text{pF}$  or equivalent (includes jig and probe capacitance)  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

**WAVEFORM : PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)**

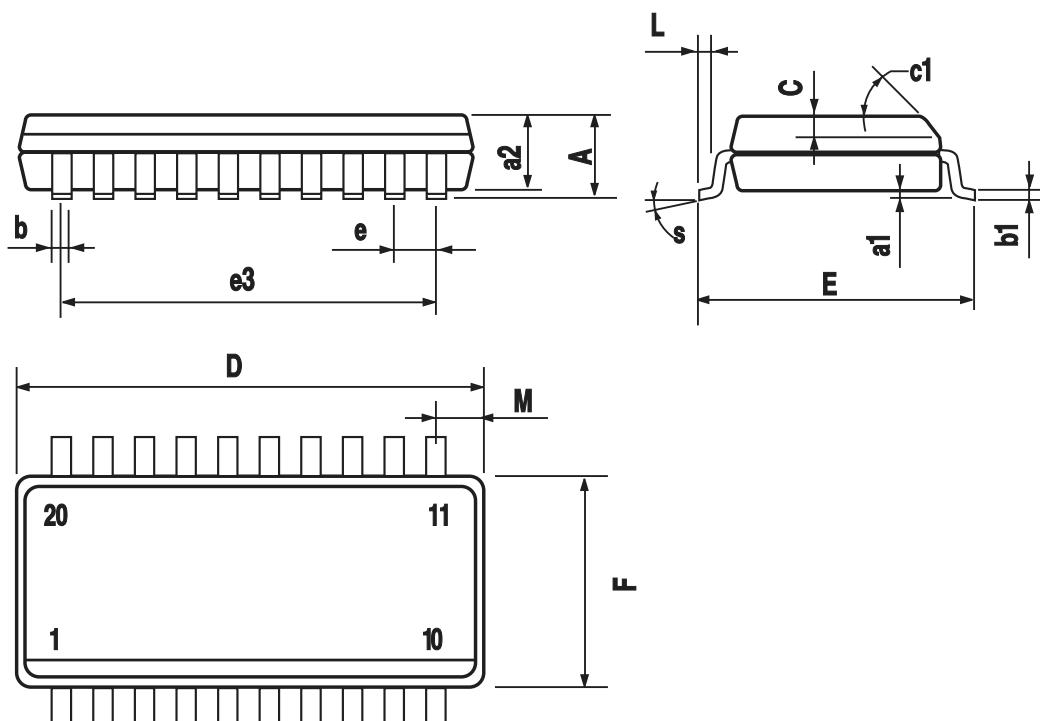
Plastic DIP-20 (0.25) MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053



P001J

## SO-20 MECHANICAL DATA

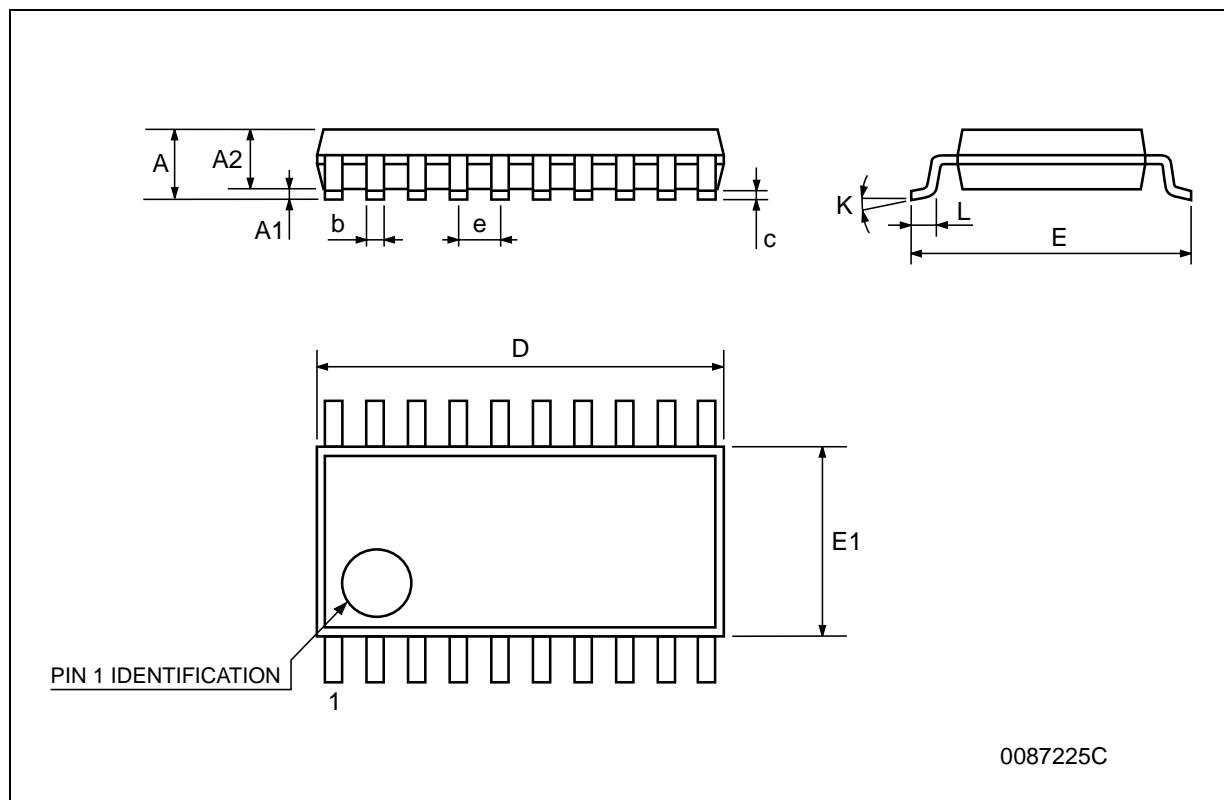
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
M			0.75			0.029
S	8° (max.)					



PO13L

## TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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